AMENDMENTS TO THE CLAIMS:

Please cancel claims 12 – 20, without prejudice or disclaimer of their subject matter. This listing of claims will replace all prior versions and listings of claims in the application:

1. (Original) A method of manufacturing a semiconductor device, comprising:

forming a metal compound film directly or indirectly on a semiconductor substrate;

forming a metal-containing insulating film consisting of a metal oxide film or a metal silicate film by oxidizing said metal compound film; and

forming an electrode on said metal-containing insulating film.

2. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film is formed of a compound that does not bring about a reaction with the semiconductor substrate or with an insulating material positioned below the metal compound film to form a compound.

3. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film has a thickness not larger than 5 nm.

4. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein formation of said metal compound film and formation of said metal-containing insulating film by oxidation of the metal compound film are repeated a plurality of times.

5. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein an insulating film selected from the group consisting of a silicon oxide film, a silicon nitride film and a silicon oxynitride film is interposed between said semiconductor substrate and said metal compound film.

6. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film is selected from the group consisting of a metal nitride film, an oxygen-containing metal nitride film, a silicon-containing metal nitride film, a metal nitride film containing both oxygen and silicon, a metal carbide film, an oxygen-containing metal carbide film, a silicon-containing metal carbide film, a metal carbide film containing both oxygen and silicon, a metal carbonitride film, an oxygen-containing metal carbonitride film, a silicon-containing metal carbonitride film, and a metal carbonitride film containing both oxygen and silicon.

7. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film contains at least one metal selected from the group consisting of titanium, zirconium, hafnium, tantalum, niobium, aluminum, yttrium and cerium.

8. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal-containing insulating film consists of a plurality of first insulating regions

formed of grains containing a metal oxide of a metal element contained in said metal compound film and a second insulating region formed of an amorphous insulating material in a region except the first insulating regions.

9. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a metal element forming said metal oxide and silicon, said first insulating region contains a crystal of said metal oxide, and said second insulating region contains silicon, oxygen and a metal element forming said metal oxide.

10. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a first metal element forming said metal oxide and a second metal element differing from said first metal element, said first insulating region contains a crystal of said metal oxide, and said second insulating region contains oxygen and said second metal element.

11. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a metal element forming said metal oxide, said first insulating region is formed of crystal grains of said metal oxide, and said second insulating region is formed of an amorphous region of said metal oxide.

12. – 20. (Canceled)